



YJL2301N

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

v



YJL2301N

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	-19			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-19V, V_{GS}=0V, T_C=25$			-1	μA
Gate Body Leakage Current	I_{GSS}	$V_{GS}=10V, V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	-0.4	-0.62	-1.0	V
Static Drain Source On Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=1.5A$		94	114	m
		$V_{GS}=-2.5V, I_D=1.2A$		130	151	
		$V_{GS}=-1.8V, I_D=1.0A$		189	219	
Diode Forward Voltage	V_{SD}	$I_S=1.7A, V_{GS}=0V$		-0.8	-1.2	V
Maximum Body Diode Continuous Current	I_S				-1.7	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		327		μF
Output Capacitance	C_{oss}			62		
Reverse Recovery Time	t_{rr}	$I_F=1.0A, V_{DR}=100V$		27		ns
Switching Parameters						
Total Gate Charge						
Gate Source Charge						
Gate Drain Charge	Q_{gd}					
Reverse Recovery Charge	Q_r					



Typical Performance Characteristics

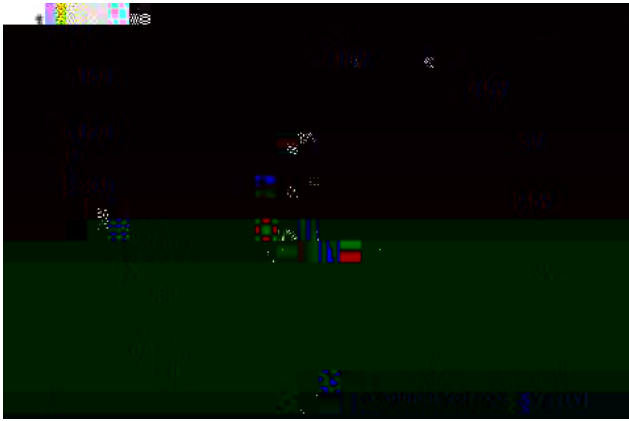


Figure1. Output Characteristics

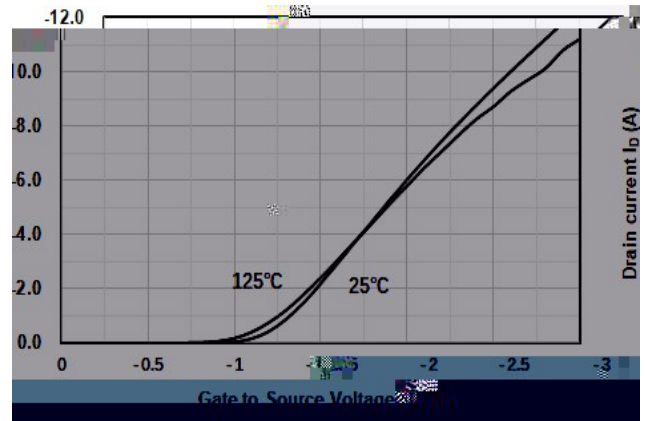


Figure2. Transfer Characteristics

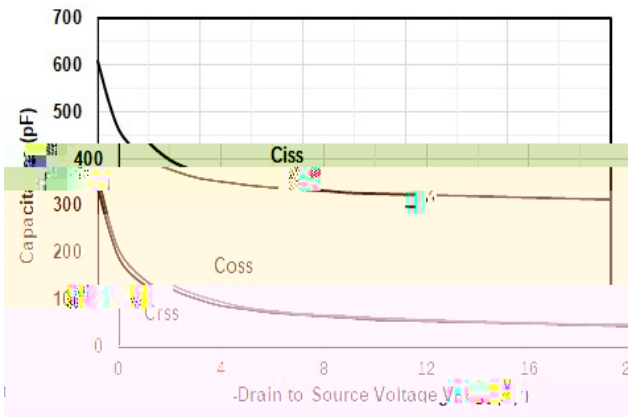


Figure3. Capacitance Characteristics

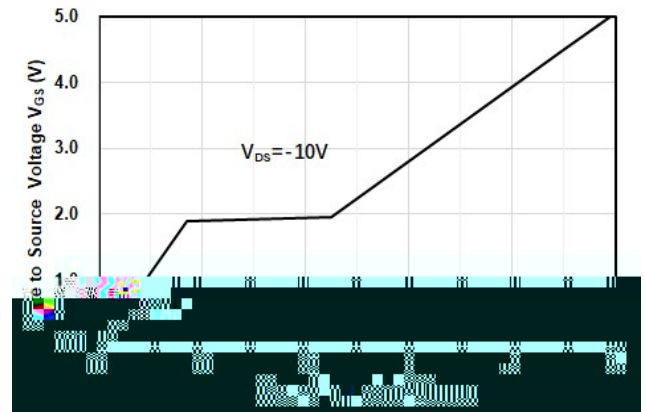


Figure4. Gate Charge

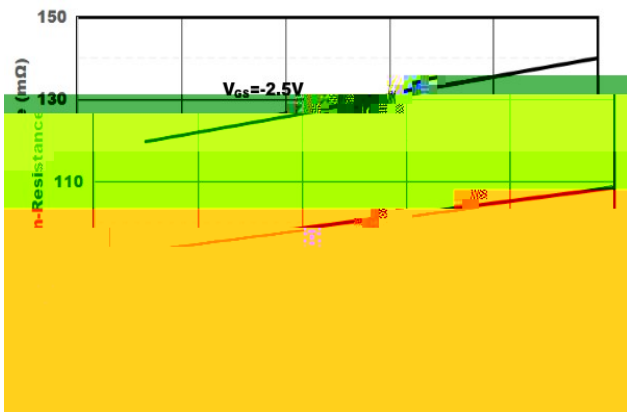


Figure5. Drain Source on Resistance

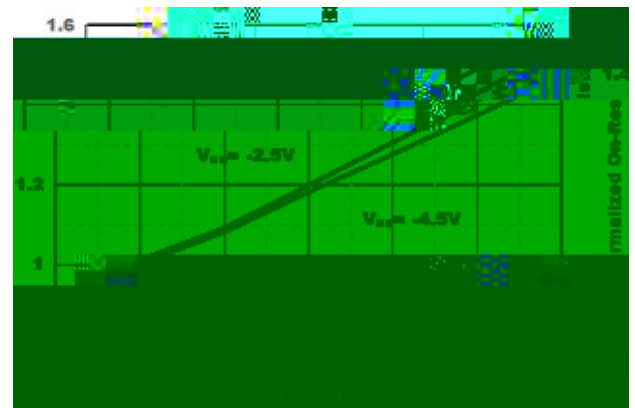


Figure6. Drain Source on Resistance

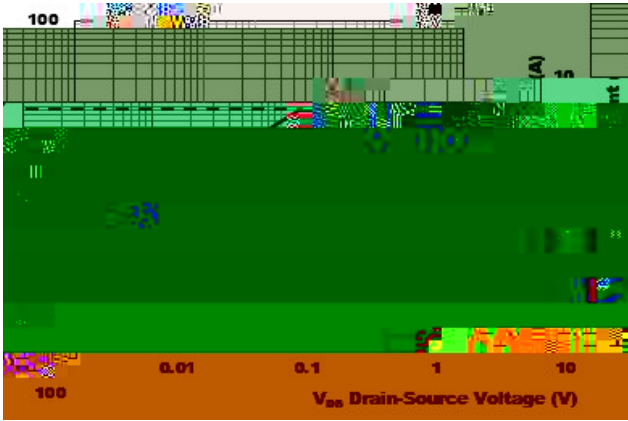


Figure7. Safe Operation Area

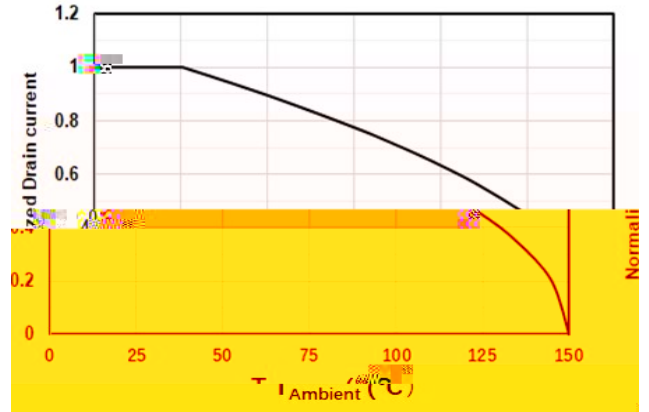


Figure8 Drain Current vs Ambient temperature

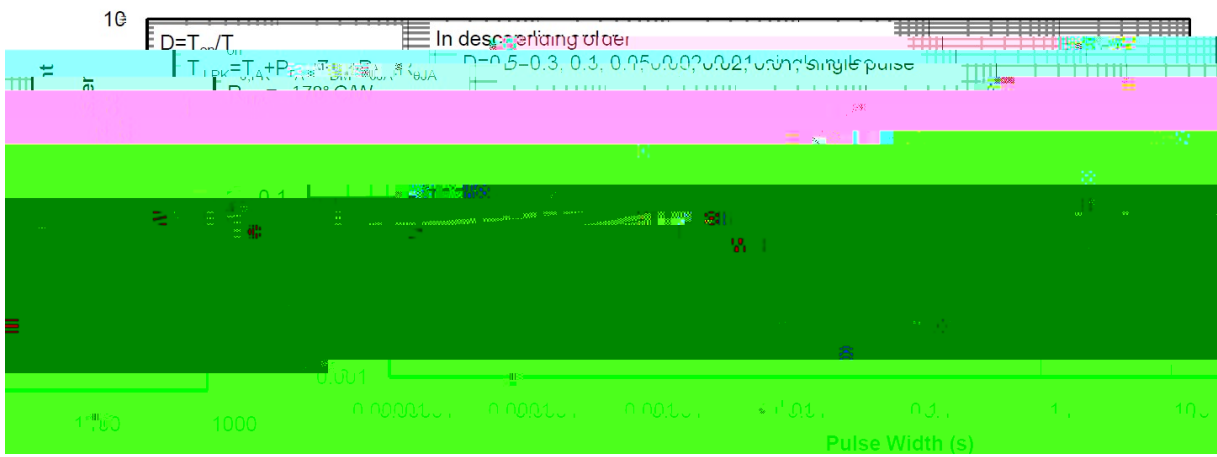


Figure9 Normalized Maximum Transient Thermal Impedance



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